Compact Itinerant Microwave Photonics with Superconducting High-Kinetic Inductance Microstrips

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Microwave photonics is a remarkably powerful system for quantum simulation and technologies, but its integration in superconducting circuits, superior in many aspects, is constrained by the long wavelengths and impedance mismatches in this platform. We introduce a solution to these difficulties via compact networks of high-kinetic inductance microstrip waveguides and coupling wires with strongly reduced phase velocities. We demonstrate broadband capabilities for superconducting microwave photonics in terms of routing, emulation and generalized linear and nonlinear networks.

Itinerant optical photonics [1–4] was made possible by the low loss, short wavelength, and controlled patterning in optical on-chip devices, enabling multimode interferometry. Aside from demonstrating superposition and multi-partite entanglement, these systems are proposed as a path to quantum-technological applications [5–7]. A clear and persistent disadvantage of these devices is the challenge of on-demand single optical photon generation [8].

In contrast, superconducting circuits accomplished high quality, on-demand single microwave photons more than a decade ago [9]. As superconducting qubit systems emerge as a leading candidate in the race towards universal quantum computing, it is vital to integrate microwave photonics for routing, processing and communication between computational nodes [10, 11].

The ubiquitous frequencies of microwave quantum circuits are constrained between $\sim 10^9$-$10^{10}$ Hz [12, 13] due to a combination of fundamental and technical considerations [14]. This leads to typical wavelengths, $\lambda$, in excess of $10\,\mathrm{mm}$ and enlarged overall device sizes, with consequent box-mode parasitic excitations and fabrication difficulties when trying to scale to complex networks of microwave photonics [15, 16]. It has been suggested to compress footprints by deforming the traces to spirals or meanders [17, 18]. However, such elongated devices are more vulnerable to fabrication errors leading to ”weak spots” [19] and increased noise from magnetic vortex penetration [20].

The high-kinetic inductance (HKI) of amorphous superconductors (such as WSi) along with a large microstrip capacitance achieves impedance-matched short wavelength microwave photonics. This fulfils the linear networking properties considered above. In addition, the nonlinearity [21, 22] of such HKI microstrips provides a route to amplification at the quantum limit [23] due to wave-mixing phenomena. This can now be extended to a multi-mode network for more complex photonic tasks.

In this Letter we establish a scalable platform for itinerant microwave networks by demonstrating a variety of geometries of superconducting HKI WSi coupled microstrips. We achieve controllable links between the 50Ω impedance-matched central traces by using sub-micronic [24] coupling traces.

The total inductance per unit length of an HKI trace is given by

$$L_l = \frac{\mu_0 \lambda_L^2}{A} \left( 1 + \left( \frac{I}{I_s} \right)^2 \right) + L_{g,l},$$

where $\mu_0$ is the vacuum permeability, $\lambda_L$ the London penetration depth, $A$ the cross section, $I$ the current,

![FIG. 1. (a) Direct and coupled transmission measurements and simulation for two parallel microstrip traces periodically coupled through highly inductive nano-wires. Inset: Graphical illustration of the device. Blue: Launchers and traces. Yellow: Coupling nano-wires. (b) Phase-dependent transmission, as CW signals are applied in both traces simultaneously, with changing input powers in port 1 (represented by colorbar) and changing phase in port 2 (horizontal axis). The measured output in port 2' (vertical axis).](arXiv:2106.15951v1 [physics.app-ph] 30 Jun 2021)
FIG. 2. Characterization of the 7PMT as described in the main text. (a) Graphic representation, also illustrating the various layers of fabrication: Si substrate (grey), WSi (green), dielectric amorphous Si (pink) and Al (purple). Top-left corner inset: Zoom, showing traces and coupling lines. Bottom-right inset: Angled top view, showing the opening in Al and Si layers, fitting the launch pad of the WSi seen as shadow. (b) Transmission spectra for signals introduced in the center waveguide, perpendicular squares marking the center of the pulse, corrected for unequal launching traces. Inset: Zoom on the (time,amplitude)-plane analogue to the colored planes in the main figure. (d) Interference measurement: Measured transmission to ports 1'-4', as we split the CW input signal at $f_{1,4} = 5.12$ GHz between port 1 and 4, varying the phase difference and relative power input. (e) Simulation showing the power in the waveguides, as we apply a CW of frequency 6 GHz in the center trace.

and $I_s$, the characteristic current scale for nonlinearity [25]. The geometric inductance per unit length, $L_{g,l}$ is negligible compared to the HKI (first term in $L_l$) for our WSi traces.

Characteristic impedance-matching is achieved in the superconducting microstrips with relative ease, since the capacitance per unit length $C_l$ can be engineered to fit $L_l$ to reach the impedance $Z = \sqrt{L_l/C_l} = 50\Omega$. This contrasts the case of coplanar HKI traces, where extended tapers are required to avoid reflections due to discontinuity in $Z$ [26]. The use of impedance-matched microstrip tapers makes the tapers superfluous, reducing the area further.

As the couplers’ widths are narrowed down to about 1/10 of the 50Ω waveguides’ width, $L_l$ of the former is increased by an order of magnitude. Following these geometric changes also $C_l$ changes its value to become smaller by the same ratio. Thus the couplers behave as mostly inductive links. The couplers’ $Z_l$ is therefore an order of magnitude larger than that of the waveguides, confirming their perturbative role as a weak link.

A fundamental advantage of the microstrip architecture is the strongly decreased phase velocity, $v_{ph} = 1/\sqrt{L_lC_l} \simeq 4 \times 10^6$ m/s in the devices presented in this letter. The immediate consequence for travelling waves (cf. in the amplifier in Ref. [23] and in the first two devices shown in this letter) is that the photons are decelerated to spend several nanoseconds in our device, permitting us to shorten the traces significantly and still maintain sufficient wave-mixing or appreciable routing to other coupled waveguides. In the case of resonant structures, waveguide lengths $L$ can be reduced according to $L = \lambda/2 \sim v_{ph}/2f$ where $f$ is the desired frequency, cf. the operational bandwidth. For our $v_{ph}$ and $f$’s this corresponds to $L \sim 200 \mu m$.

Our devices are fabricated by four consecutive lithographic steps, and intermediate etching and evaporation procedures [27]. The final products are $6 \times 6 \text{mm}^2$ chips with microstrip circuits coated by Al film, serving both as a ground plane and to protect the device mechanically during continued handling. After wire-bonding to impedance-matched printed circuit boards and mounting in Al boxes, all experiments are conducted at $\pm 20 \text{ mK}$ temperatures in our dilution refrigerator, far below WSi’s critical temperature of 4.7 K [28].

On the first device we measure the output in both of two parallel $3\mu m$ wide microstrips, separated by $30\mu m$, and connected every $100\mu m$ by couplers, when constant waves (CW) signals are applied from our Keysight P5024A Vector Network Analyzer into one of them (see Fig. 1(a)). The total length of each microstrip, i.e. from launcher to launcher, is $3 \text{ mm} > \lambda \simeq 400 \mu m$. The un-employed launcher (port 2 in Fig. 1(a)) is terminated to the ground through attenuators and a 50 Ω resistor at room temperature to avoid reflections into the waveguide. Our simulations, based on voltage continuity and current conservation, quantitatively predict the frequency-dependent transmission of this circuit [29]. Characteristic features, such as the flat region at low frequencies and the alternating transmission peaks and dips, can be linked to the band structure of the corresponding peri-
FIG. 3. Characterization of the 2DSL. (a) Optical microscopy image (false colored), showing parts of wide microstrip resonators coupled with narrow couplers. Inset: SEM photo of coupling to input or readout with colors matching Fig. 2 (grey substrate and green WSi visible in the gap separating purple readout line from purple ground). Transmission vs. frequency normalized by the linear simulation (see Fig. 3(c)), which considers dielectric loss and the transmission profile of attenuators, amplifiers, and circulators applied in the experiment. In this device, we boost the couplers’ $Z_l$ further by removing the ground above them (not shown), hence minimizing their $C_l$. The performance is tested by applying CW signals over a bandwidth of 6 GHz in the center trace (no. 4) and measuring the output, presented in Fig. 2(b). Here the broken vertical line marks the frequency $f_{1,4} = 5.99$ GHz, chosen for the subsequent measurement, since there is significant amplitude of transmission to all other ports. We then replace the CW signal with short gaussian-shaped wave packets generated by side-band mixing control, again introduced in the center trace. Their arrival is detected at the output terminals of the device; it takes nanoseconds to transverse the network, but when subtracting the electrical delay, we register the arrival with a delay of $\sim 10-30$ ps (see Fig. 2(c)), compared to the arrival of the first pulse at port $4'$. In this figure, the smaller amplitude of the detected pulse at port $3'$ (shown in red) is consistent with the slightly deteriorated transmission through that specific trace (inset in Fig. 2(b)).

Returning to CW signals, we proceed at the frequency $f_{1,4} = 5.12$ GHz for which the eight transmissions ratios from ports 1 and 4 to ports $1'-4'$ (according to annotation in Fig. 2(a)) are all relatively high and similar in magnitude. Splitting the input power between the former two, we vary the relative phase and measure the output in Fig. 2(d). The nearly symmetrical interference patterns are due to similar transmission coefficients in the network (e.g. $4 \rightarrow 1'$ vs. $1 \rightarrow 4'$). Injection at port 4 has the possibility also to coherently diffuse to traces $5'-7'$, causing the slight asymmetries in Fig. 2(d).

We conclude the study of the 7PMT’s linear behavior by simulating the spatial power distribution in the device, not directly measurable with our current setup. Nevertheless, the result in Fig. 2(e) resembles numeric results for quantum walks [31], with consequent applications also for quantum photonics [32].

The third and final demonstration of the capabilities of superconducting microstrip WSi circuitry switches the focus from travelling to standing waves in a 2D square lattice (2DSL) consisting of 49 microstrips, effectively acting as a multi-mode resonance cavity. Each microstrip resonator is $\sim 400 \mu$m long and is coupled to four neighbors (two in either end as shown in Fig. 3(a)). The resonators in the two opposing corners of the 2DSL are capacitively coupled to coplanar transmission lines (see inset of Fig. 4(a)), terminated in large ($0.3 \text{ mm wide}$) launchpads, enabling excitation and measurement. Scanning CW the transmission spectrum (plotted in Fig. 3(b)) reveals three distinctive energy bands within the operational bandwidth of our readout-chain, comparable to the linear simulation (see Fig. 3(c)), which considers both dielectric loss and the transmission profile of attenuators, amplifiers, and circulators applied in the exper-
FIG. 4. (a) Power transmission in the 7PMT through trace 1, (b) from port 1 to port 4', and (c) through trace 4. The labels follow the notation in Fig. 2(a). The color-scale is common for all three subfigures, and indicates the power dependent transmission normalized to the transmission of the lowest power ($P_{\text{min}}$) in the spectrum. (d) Nonlinearity of the 2DSL measured by a polar representation of the transmission $S_{21}$ in one of the peak frequencies from Fig. 3(b) (inset: simulation) and (e) magnitude of the transmission around the same peak frequency as shown in (d) (inset: simulation).

The simulation, analogue to that in Fig. 1(a), also correctly draws out smaller features within the energy bands (Fig. 3(d)).

The 2DSL’s geometry is closely related to that of photonic gratings employed to demonstrate a variety of many-body problems [33], such as quantum entanglement [34], interacting polaritons [35], and phase transitions of Mott-Insulators [36, 37].

We elaborate further on future applications of this system by re-writing the state in which only the input resonator is excited (in the following described by the state $\chi(0)$) as a linear superposition of eigenmodes $\psi_m$ in the second energy band in Fig. 3(d) (between 4-8 GHz). Driving such a single site excitation requires a large instantaneous bandwidth of about 1.5 GHz (beyond the current capabilities of our IQ mixers), but it would produce the energetic map shown in Fig. 3(e). We numerically propagate the time-dependent state $\chi$ according to $\chi(t) = \sum_m \alpha_m \psi_m e^{-i\omega_m t}$ where $\omega_m = 2\pi f_m$, with $f_m$ being the frequency of the $m$’th peak, and $\alpha_m$ are the superposition coefficients of $\chi(0)$. As the excitation evolves throughout the lattice [Figs. 3(e)-(h)], it preserves a certain degree of localization. The evolution is visualized in the supplemental information [38].

Finally, we measure the nonlinearity in our devices emerging from the HKI of WSi by transmitting CW of increasing powers through chosen waveguides in the 7PMT and through the 2DSL, starting at signals corresponding to an occupation of $\sim 1$ photons in the device. The frequency transmission spectra of the former, plotted in Figs. 4(a)-(c) emphasize that the nonlinearity commences in the couplers before in the waveguides. The direct transmission $S_{1 \rightarrow 1'}$, is thus hardly affected until the highest excitations are reached and the signal is confined in the trace. Transmitting power from this waveguide to the center of the device relies on couplers between all waveguides in between, resulting in the more power dependent $S_{1 \rightarrow 3'}$. The case of transmission through the central waveguide (trace 4) differs from the two above: Despite again considering a coupler-free transmission path, this waveguide is coupled on either side and hence it is more sensitive to the couplers’ behaviour. Also in the 2DSL nonlinearity is observed, when we introduce sufficiently strong powers and affect the resonance frequencies’ phase and magnitude (exemplified in Figs. 4(d) and (e) respectively) which can be explained by a Duffing-type toy-model (see insets and [39]).

Our measurements span several orders of magnitude in power at the devices, starting from $P = -120$ dBm, which corresponds to an expectation of 0.2 photons within our device (given by $PL/(h\nu_{ph})$, with $h$ Planck’s constant, $f = 6$ GHz and $L = 3$ mm for the 7PMT traces). Remarkably, the nonlinearity of the couplers confines the transmission in Fig. 4(b) at $-90$ dBm corresponding to only 200 photons.

The use of a thin dielectric barrier for the microstrip capacitance leads to losses from two-level-systems in the material [40–42]. However, the short length (up to 10’s of wavelengths) of the itinerant devices ensures minimal losses ($\lesssim 10\%$) when using a low loss-tangent ($< 2 \times 10^{-4}$) barrier material such as amorphous Silicon. In future designs an alternative dielectric could replace amorphous Si to allow even higher transmissions and thus signals closer to the single-photon-limit.

In summary, with established clean room procedures and utilizing the HKI of WSi in a microstrip geometry, we have introduced a platform for on-chip microwave photonic experiments. We believe the opportunities with our methods reach beyond what we have shown here to include e.g. additional geometries, homodyne tomography, and multimode interferometry. Specifically, applications subject to minor modifications of the devices, include scattershot boson-sampling [43], Hawking radiation [44], and reservoir-computing in neural networks [45]. We acknowledge the support of ISF Grant Nos. 963.19 and 2323.19 and of the DFG Grant No. AN336/13-1, the IQST, and the Zeiss Foundation.
[27] See Supplemental Material, Section D at [URL will be inserted by publisher] for the full fabrication recipe.
[29] See Supplemental Material, Section B at [URL will be inserted by publisher] for a detailed description of the simulation.
[30] In the Supplemental Material Section E we elaborate further on the nonlinearity in this device [URL will be inserted by publisher].
[32] In the Supplemental Material Section E we elaborate further on this simulation, also including the power flow through the couplers [URL will be inserted by publisher] for more information of this simulation and a short video on the propagation.
[38] See Supplemental Material, Section F at [URL will be inserted by publisher] for more information of this simulation and a short video on the propagation.
[39] See Supplemental Material, Section H [URL will be inserted by publisher].
A. Estimating the phase velocity $v_{ph}$

An important property of our microstrip networks is the phase velocity, $v_{ph}$ which depends on frequency and geometry of the traces. For the couplers, the geometric inductance, $L_{geo}$ is completely negligible, and so $L_l = \mu_0 \lambda^2 / (t \cdot w)$, where $\mu_0$ is the vacuum permeability, $\lambda$ the superconducting penetration depth, and $w$ and $t$ are the width and thickness of the trace in question. Furthermore $C_l \propto w$, so for traces with submicronic ranges, $v_{ph} = (C_l L_L)^{-1/2}$ is independent of $w$. However, in wider traces such as our wave guides, $L_{geo}$ becomes important, hence raising the total $L_l$ somewhat, and lowering $v_{ph}$ by $\sim 10\%$. Wave-guides and couplers are therefore foremost differentiated by their $Z$.

We estimate $\lambda_{WSi} \sim 450nm$ for our sputtered $W_{0.55}Si_{0.45}$ based on other measurements (not shown here), which is in the same order of magnitude, but moderately lower than more tungsten-rich alloys [1].

Our measured $v_{ph}$ fit its theoretical value found using the formulae and values in this section, and the results also agrees with the computed microstrip $v_{ph}$ from [2].
B. Crystal model for integrated microwave optics

Aiming towards functionalizing high-kinetic inductance microstrip networks forming periodic one- or two-dimensional structures are of obvious interest. Such structures are favorably described and analyzed in the language of crystal physics, i.e., we should think about Bloch-waves and their band structure.

Here, we present such a description for the linear behavior of the double-trace structure (easily extendable to multi-trace or full two-dimensional devices). To guarantee accessibility for a general audience, we will use formulations and derivations familiar from scattering problems in textbook quantum physics, while refraining from relying on knowledge or methods from specialized microwave engineering literature (see e.g., Ref. [3] for an introduction). We aim in this section not at the most efficient and general simulation, but rather for insight into the underlying physics. This lays the groundwork for better design and serves as starting point for more advanced descriptions (including nonlinearities and quantum effects).

We start from a description of voltage and current traveling along the various segments, see Fig. S1(a),

\[ V_{\alpha}^l(x_\alpha) = t_{\alpha}^l e^{ik_\alpha x_\alpha} + r_{\alpha}^l e^{-ik_\alpha x_\alpha} \quad \text{where} \quad \alpha = p, s, c; \quad l = 1, 2, \ldots, N \quad (S1) \]

\[ Z_{\alpha} I_{\alpha}^l(x_\alpha) = t_{\alpha}^l e^{ik_\alpha x_\alpha} - r_{\alpha}^l e^{-ik_\alpha x_\alpha} \quad \text{with} \quad k_\alpha = 2\pi f \sqrt{L_{\alpha} C_{\alpha}} \quad \text{and} \quad Z_\alpha = \sqrt{L_{\alpha}/C_{\alpha}}. \quad (S2) \]

The different segments are distinguished by an index \( l \) numbering the unit cells and \( \alpha = p, s, c \) for primary, secondary and coupler lines. A standard transmission line model yields the parameters for the wave propagation along the segments, where dissipation can also easily be included. For the designed double line, we can assume \( Z_p = Z_s =: Z_0, \quad k_p = k_s =: k_0 \), while \( x_{p/s} \in [0, L] \) and \( x_c \in [0, d] \).

We now introduce specific variables for the voltages on the nodes of the networks, \( v_{p/s}^l \), so that, for instance:

\[ v_p^l = V_{p}^{l-1}(L) = t_p^{l-1} e^{ik_p L} + r_p^{l-1} e^{-ik_p L} \quad (S3a) \]

\[ v_p^{l-1} = V_{p}^{l-1}(0) = t_p^{l-1} + r_p^{l-1}. \quad (S3b) \]

In these variables the Kirchhoff circuit equations for voltages are fulfilled by construction, while to evaluate the Kirchhoff current equations we have to rewrite the currents in the
FIG. S1. (a) Sketch of the double-trace structure and definitions introduced in the text. Using the voltages on the nodes \(v^l\) as variables, Kirchhoff rules yield a tight-binding model with parameters \(\epsilon, h_0, c\) as marked on the rightmost unit cell. (b) The Fabry-Perot resonator formed by scatterers describing in/out-coupling and propagation in an eigenmode of the infinite line.

voltage node variables using Eq. (S3), e. g.,

\[
Z_0 I_p^{l-1}(L) = t_p^{l-1} e^{ik_0 L} - r_p^{l-1} e^{-ik_0 L} = v^l_p e^{ik_0 L} + e^{-ik_0 L} - v^{l-1}_p e^{ik_0 L} - e^{-ik_0 L} = v^l_p \frac{z_0 + \bar{z}_0}{z_0 - \bar{z}_0} - v^{l-1}_p \frac{2}{z_0 - \bar{z}_0} ,
\]

The Kirchhoff current equations,

\[
I_p^{l-1}(L) - I_p^l(0) - I_c^l(0) = 0 \quad \text{current conservation in upper node} \quad (S5a)
\]

\[
I_s^{l-1}(L) - I_s^l(0) + I_c^l(d) = 0 \quad \text{in lower node} \quad (S5b)
\]

when rewritten in term of the voltage node variables using, e.g., Eq. (S4),

\[
0 = v^{l-1}_p \frac{2z_0}{Z_0 1 - z_0^2} + v^l_p \left( \frac{-21 + z_0^2}{Z_0 1 - z_0^2} + \frac{-11 + z_0^2}{Z_c 1 - z_c^2} \right) + v^{l+1}_p \frac{2z_0}{Z_0 1 - z_0^2} + v^l_p \frac{2z_c}{Z_c 1 - z_c^2} \quad (S6a)
\]

\[
0 = v^{l-1}_s \frac{2z_0}{Z_0 1 - z_0^2} + v^l_s \left( \frac{-21 + z_0^2}{Z_0 1 - z_0^2} + \frac{-11 + z_0^2}{Z_c 1 - z_c^2} \right) + v^{l+1}_s \frac{2z_0}{Z_0 1 - z_0^2} + v^l_s \frac{2z_c}{Z_c 1 - z_c^2} \quad (S6b)
\]
immediately suggest a tight-binding picture with real parameters
\[
\begin{align*}
\epsilon &= i \left(\frac{2}{Z_0} \frac{1 + z_0^2}{1 - z_0^2} + \frac{1}{Z_c} \frac{1 + z_c^2}{1 - z_c^2}\right) \quad \text{site energy} \\
\h_0 &= -i \frac{1}{Z_0} \frac{2z_0}{1 - z_0^2} \quad \text{in-line hopping} \\
\h_c &= -i \frac{1}{Z_c} \frac{2z_c}{1 - z_c^2} \quad \text{cross-line hopping}
\end{align*}
\] (S7) (S8) (S9)

Eigenmodes and band structure of the infinite double-line
The eigenmodes of an infinite double-line are straightforwardly found by an ansatz
\[
\begin{pmatrix}
\psi_p^l \\
\psi_s^l
\end{pmatrix} =
\begin{pmatrix}
p \\
s
\end{pmatrix} e^{iKl} ; K \in \mathbb{C}
\] (S10)
as eigensolutions of
\[
\begin{pmatrix}
\epsilon + 2\h_0 \cos K & \h_c \\
\h_c & \epsilon + 2\h_0 \cos K
\end{pmatrix}
\begin{pmatrix}
p \\
s
\end{pmatrix} = 0 \quad \Rightarrow \cos K_{1/2} = -\frac{\epsilon}{2\h_0} \pm \sqrt{\frac{\h_c^2}{4\h_0^2}}
\] (S11)
with eigenvectors that are (anti-)symmetric in primary and secondary voltages.

Figure S2(a) shows the (real and imaginary parts of the) eigenvalues \(K_{1/2}\) versus frequency with range and parameters as in Fig. 1(a) of the main text. It corresponds to a dispersion relation \(\omega(K)\) for the quasi-wavevector \(K/L\) of a Bloch-wave. Apparent from Fig. S2, there is a band gap for the asymmetric solution below 3.8 GHz, where only an evanescent wave solution with \(\text{Im} K_1 > 0\) exists. The symmetric solution (with equal voltages at both ends of each coupler) is barely influenced by the couplers and \(K_2 \approx kL\).

Here, we will not discuss further how the band structure depends on device parameters and how to design it, but will concentrate on how features of the band structure (of the infinite double-line) affect the transmission through the finite line. For that, in- and out-coupling to the eigenmodes at the boundaries of the double-line device are crucial.

In- and out-coupling to eigenmodes
The symmetry of the double-line device with respect to exchanging primary and secondary line is reflected in the (anti)symmetric eigenmodes we found above. If the lines are fed by a symmetric combinations of incoming waves, these will couple to the symmetric eigenmode
FIG. S2. (a) Band structure of the double-line structure. The (Bloch-)wavevector $K_2 \approx kL$ of the
eigenmode symmetric in primary and secondary line is nearly unaffected by the couplers, while the
anti+symmetric mode has a band gap where $\text{Im} K_1 > 0$.

Transmission of symmetric (b) and antisymmetric (c) eigenmode through the Fabry-Perot struc-
ture, cf. Eqs. (S18) and (S19). (d) Total transmission for direct ($1 \rightarrow 2$) and cross-transmission
($1 \rightarrow 4$) resulting from constructive and destructive interference of the (anti)symmetric transm-
sions, see Eq. (S20).

and result in symmetric outgoing waves. In that manner, the double-line decouples into two
independent single-channel problems.

Formally, we start by solving Eq. (S3) for the left/righ-going amplitudes of unit cell $l - 1,$
\[
\begin{align*}
t^{l-1}_\alpha &= \frac{1}{1 - z_0^2} (v^{l-1}_\alpha - z_0 v^l_\alpha) 
\quad \text{(S12a)} \\
r^{l-1}_\alpha &= \frac{1}{1 - z_0^2} (-z_0^2 v^{l-1}_\alpha + z_0 v^l_\alpha) , \quad \text{where } \alpha = p/s , 
\quad \text{(S12b)}
\end{align*}
\]

where the input and output of a line with \(N\) nodes is
\[
\begin{align*}
t^L_\alpha &= t^0_\alpha , \quad r^L_\alpha = r^0_\alpha , \quad t^R_\alpha = z_0 t^N_\alpha , \quad r^R_\alpha = z_0 r^N_\alpha . 
\quad \text{(S13)}
\end{align*}
\]

With the ansatz for the general solution
\[
\begin{pmatrix}
  v^l_p \\
  v^l_s
\end{pmatrix} = a_1 e^{iK_1l} \begin{pmatrix} 1 \\ -1 \end{pmatrix} + b_1 e^{-iK_1l} \begin{pmatrix} 1 \\ -1 \end{pmatrix} + a_2 e^{iK_2l} \begin{pmatrix} 1 \\ 1 \end{pmatrix} + b_2 e^{-iK_2l} \begin{pmatrix} 1 \\ 1 \end{pmatrix} 
\quad \text{(S14)}
\]

this results in
\[
\begin{align*}
t^l_\alpha (1 - z_0^2) &= \pm a_1 e^{iK_1l} (1 - z_0 e^{iK_1}) \pm b_1 e^{-iK_1l} (1 - z_0 e^{-iK_1}) + a_2 e^{iK_2l} (1 - z_0 e^{iK_2}) + b_2 e^{-iK_2l} (1 - z_0 e^{-iK_2}) 
\quad \text{(S15a)} \\
r^l_\alpha \frac{1 - z_0^2}{z_0} &= \pm a_1 e^{iK_1l} (e^{iK_1} - z_0) \pm b_1 e^{-iK_1l} (e^{-iK_1} - z_0) + a_2 e^{iK_2l} (e^{iK_2} - z_0) + b_2 e^{-iK_2l} (e^{-iK_2} - z_0) . 
\quad \text{(S15b)}
\end{align*}
\]

After introducing (anti)symmetric combinations,
\[
\begin{align*}
t^l_+ &= \frac{t^l_p + t^l_s}{2} = \frac{1}{1 - z_0^2} \left[ a_1 e^{iK_1l} (1 - z_0 e^{iK_1}) + b_2 e^{-iK_2l} (1 - z_0 e^{-iK_2}) \right] 
\quad \text{(S16a)} \\
t^l_- &= \frac{t^l_p - t^l_s}{2} = \frac{1}{1 - z_0^2} \left[ a_1 e^{iK_1l} (1 - z_0 e^{iK_1}) + b_1 e^{-iK_1l} (1 - z_0 e^{-iK_1}) \right] 
\quad \text{(S16b)}
\end{align*}
\]

and equivalent expressions for \(r^l_\pm\), so that we indeed arrive at two decoupled single-channel scattering problems.

We can solve, e.g., the symmetric problem by eliminating \(a_2\) and \(b_2\) from the four equations, resulting from taking Eq. (S16a) and the corresponding equation for \(r^l_+\) at \(l = 0, N\), which using Eq. (S13) yields the total scattering matrices,
\[
\begin{pmatrix}
  r^L_\pm \\
  t^L_\pm
\end{pmatrix} = \hat{S}^{\text{tot}}(K_{2/1}) \cdot \begin{pmatrix}
  t^L_\pm \\
  r^R_\pm
\end{pmatrix} . 
\quad \text{(S17)}
\]

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This way, one finds for instance,

\[ t^{\text{tot}}(K) = \frac{(1 - z_0^2) \sin K}{\bar{z}_0 \sin [K(N + 1)] - 2 \sin [KN] + z_0 \sin [K(N - 1)]}, \] (S18)

which is displayed in Fig. S2(b,c) for the symmetric and antisymmetric single-channel problem.

**Fabry-Perot picture**

To understand this result, it is instructive to view the single-channel problem as a Fabry-Perot type scattering problem, where in- and out-coupling constitute a left and right scattering barrier of a resonator, in which propagation is described by the eigenmode. Transfer matrices of the individual barriers, \( \tilde{T}_{L/R}(K_{1/2}) \), are then readily gained from Eq. (S16) (and the corresponding equation for \( r_{L/R} \)) and Eq. (S18) is recovered from the standard picture of multiple reflections

\[ t^{\text{tot}}(K) = \tilde{t}_L e^{iK(N-1)} \left( 1 + \tilde{r}_R e^{i2K(N-1)} \tilde{r}_L' + \ldots \right) \tilde{t}_R = \frac{\tilde{t}_L e^{iK(N-1)} \tilde{t}_R}{1 - \tilde{r}_R e^{i2K(N-1)} \tilde{r}_L'}, \] (S19)

where \( \tilde{t}_{L/R}, \tilde{r}_{L/R}, \tilde{r}'_{L/R} \) are entries of the scattering matrices corresponding to \( \tilde{T}_{L/R}(K_{1/2}) \).

This picture allows us to explain the features observed in the total transmissions of the symmetric and antisymmetric single-channel problem shown in Fig. S2(b,c). In the symmetric case, where the eigenmode wavevector \( K_2/L \approx k \) (cf. Fig. S2), in- and out-coupling occurs with minute reflections, so that the total transmission \( t^{\text{tot}}(K_2) \approx 1 \) with tiny Fabry-Perot oscillations determined by the \( e^{i2K_2(N-1)} \) phase factor in the denominator. In the antisymmetric case, below the bandgap (cf. Fig. S2(a)) total transmission is completely suppressed, while above the bandgap large reflection at the in- and out-coupling 'barriers' yield pronounced anti-resonances, which become reduced as \( K_1 \) grows to approach \( kL \). The frequency of oscillations is related to the slope of the \( \text{Re} K_1(\omega) \) curve in Fig. S2(a).

**Transmission of the double-line**

From the results above for the total transmission for (anti)symmetric input, the general scattering matrix is easily constructed. For the case of a single input into the primary line (and all other inputs set to zero), one finds

\[ t^{R}_{p/s} = \frac{t^{\text{tot}}(K_2) \pm t^{\text{tot}}(K_1)}{2} t^L_p. \] (S20)
The results shown in Fig. S2(d) match numerical simulations gained from models adoptable to generic devices, which we used for the comparisons to the experimental data (in the main text), but moreover important features are now readily traceable to the underlying physical phenomena. In the bandgap of the antisymmetric solution, where $\text{Im}K_1 > 0$, sizeable transmission only occurs through the symmetric eigenmode with $|t_{\text{tot}}(K_2)| \approx 1$ and, hence, $|t_{p/s}^R| \approx 1/2$. Far above the bandgap, both eigenmodes transmit near perfectly in a wide frequency range and alternately interfere constructively and destructively in primary and secondary line, where the frequency of this interchange is determined by the difference in $K_1 - K_2$ stemming from the $e^{2K_1/2(N-1)}$ phase factors in the numerators of Eq. (S19).

Beside the large-scale structures in Fig. S2(d), this result in a coherent swap of power between primary and secondary line, while the excitation propagates along the double-line (not shown), familiar from directed couplers design in integrated fibre optics.

Just above the bandgap, substantial interference can only occur, when the antisymmetric transmission peaks due to a Fabry-Perot resonance, but it will also depend on the respective phases. These resonances are closely spaced (cf. Fig. S2(c)), and the result is the rather complex transmission pattern between 3.6 and 4 GHz.

Similar considerations as for the double-line can be employed for multi-line setups, but beyond the band structure and some symmetry considerations on the eigenmode structure, an intuitive understanding becomes considerably harder.

C. Simulation of the lattice structure

The simulation of the lattice (Fig. 3 in the main letter) employs the Kirchoff equations as detailed in Section B. But here we regard excitations as standing waves rather than travelling waves, and to ensure generality, we simulate the frequency-dependent behaviour of this device without a global direction, but instead with in- and out-going voltages and currents in every node.

Nodes are, as in Section B, the intersections between nano-wires and the wider main traces. In particular, for the lattice, nodes are the ends of resonators, i.e. are any point combining orange and blue lines (cf. Fig. S3). Edges on the other hand, we define as either main traces or nano-wire couplers, in principle only distinguished by their impedances (determined by different widths), $Z_0$ or $Z_c$, and lengths, $L$ and $d$, for main traces/couplers.
respectively. For the $q$’th node, we consider the voltage in the $j$’th edge (of all $J_q$ edges connected to this node). The edge voltage with respect to the node then can be written (in line with Eq. (S3)):

$$V_q(x) = A^j_q e^{ik_jx} + B^j_q e^{-ik_jx}$$  \hspace{1cm} (S21)

where $x$ denotes the distance from the $q$’th node along the $j$’th edge and $k_j$ is the impedance and frequency dependent wave-number.

We solve for $A^j_q$ and $B^j_q$ for all $Q$ nodes’ $J = \sum_q J_q$ connected edges, but the number of unknowns can be reduced by mapping the connectivity:

$$A^j_{q_1} = B^j_{q_2} e^{ik_j\delta_j}$$  \hspace{1cm} (S22)

if the $j$’th edge connects the nodes indexed $q_1$ and $q_2$ and has the length $\delta_j$. The input and output nodes (injection and readout) constitute the boundary conditions. For all other nodes, Eq. (S5) requires that

$$\sum_{j=1}^{J_q} A^j_q = \sum_{j=1}^{J_q} B^j_q$$  \hspace{1cm} (S23)

We encode Eqs. S21-S23 together with the boundary conditions in a matrix, $M$, in which each row represents an equation, so that

$$M \times \tilde{V} = \tilde{K}$$  \hspace{1cm} (S24)

where $\tilde{V} = (A^1_1, B^1_1, A^1_2, B^1_2, \ldots, A^1_Q, B^1_Q, A^2_1, B^2_1, \ldots, A^J_Q, B^J_Q)$, i.e. the vector of unknowns, and $\tilde{K}$ is a vector almost exclusively of zeros due to the nature of the equations, except for those regarding the boundary conditions.

FIG. S3. Schematic illustration (not in scale) of the 2DSL displayed with only 25 and not all 49 resonators. Blue: Main traces (3 $\mu$m wide), orange: Nano-wire couplers.
Our simulation accounts for dielectric losses as we add an imaginary term to $k_j$, taking the loss tangent of our dielectric (to be further discussed in Section D) to be $\tan\delta_0 = 5 \times 10^{-4}$.

Since our experimental setup, described in [4], includes attenuators, circulators, splitters, switches, amplifiers and a few meters of coaxial cables, the transmission alternates by a few dB throughout the bandwidth in which we measure the transmission.

D. Fabrication

All three devices described in the Letter are produced in the clean room facility by multiple deposition and patterning steps. In this section we outline the process: Initially, a $\approx 10\,nm$ WSi film is sputtered on a high resistivity ($\rho > 10^5\Omega cm$) Si substrate, and is patterned by optical laser lithography and wet-etch, leaving the intended wave-guide microstrips and the couplers with identical widths (Fig. S4(a)-(b)). After removal of the remaining photo-resist, we open a protective PMMA mask by e-beam in two windows around the intended couplers and repeat the step of wet-etch to obtain coupler-widths of $\approx 300\,nm$, below the laser-writer’s wavelength (Fig. S4d). Note that in this step we remove only the superfluous parts of the couplers, while the vast surface is covered. Next, a dielectric layer is evaporated on top of WSi as well as the remaining areas of the Si substrate, with a height carefully chosen ($\approx 30\,nm$, depending on the exact width of the wave-guides, which tends to deviate by $\pm 100\,nm$ from design due to the limited resolution of the laser writer).

We choose evaporated amorphous Si (aSi) as our dielectric material due to two of its properties: 1) The loss tangent $\tan\delta$, as mentioned above, is smaller than other available materials [3, 5]. 2) Its permittivity $\epsilon_r$, which is close to well-known values of $\epsilon_r^{Si}$ (depends weakly on morphology) regulates $C_l$ together with the thickness of this layer. [6].

For the first two devices described in this letter, the aSi is opened by liftoff above the WSi launchers (not shown in Fig. S4. This allows galvanic contact with the more robust Al launchers suitable for wire-bonding. The last device is a resonant structure and thus does not require continuous transmission lines. In a final lithographic step, we again apply a photoresist mask (this time a double-layer), evaporate a global Al ground plane and by liftoff we isolate launcher pads from the grounds (Fig. S4(g)). This completes the fabrication, and after dicing the samples are bonded to a PCB, mounted in an Al box and to our dilution fridge for cryogenic measurements.
FIG. S4. Fabrication steps illustrated with disproportional dimensions to enhance readability. Upper row: Cross-section, bottom row: Top view. (a) On the 300µm thick Si substrate (grey), 10nm WSi (yellow) is sputtered and a protective photoresist mask (red) is applied. (b) Wet-etch removes the vast majority of WSi, leaving main traces and intended couplers with similar widths. (c) An additional lithographic step is performed with PMMA (purple), stripped only at windows on either side of the couplers. (d) Wet-etch narrows down the coupler widths, while main traces are untouched. (e) The dielectric layer (partly transparent green) is evaporated unto the sample, and a new protective photoresist mask (red) is patterned. For this and the following step we display a different part of the device: Around the launcher and far away from the couplers (note that the "Si" tag is translated). (f) Evaporation of Al (transparent blue) covers the wafer. This layer is, unlike the dielectric amorphous Si, in reality opaque. (g) After lift-off in NMP and sonication, the device’s top ground plane is isolated from the launchers. The intentionally shown slight misalignment, which unavoidably arises from optical lithography, causes only very short discontinuities without $Z = 50\Omega$.

E. Simulation of the nonlinear behaviour of the double-trace device

In the main text we discussed the interference between two inputs in the double-trace device and showed the impact of nonlinear effects at higher power in Fig. 1(b). Here, we will briefly describe, how such effects can be modeled and explained.

The nonlinearity of the high-kinetic inductance in the WSi microstrips can be described [7] by a nonlinear inductance,

$$L_{\text{kin}} = L_0 \left(1 + \left(I/I^*\right)^2\right),$$

where the nonlinear coefficient scales with a current $I^*$ which is comparable to the critical current of the trace. The power dependence of $L_{\text{kin}}$ leads to a power-dependent wave-equation, which, in general, leads to frequency mixing (as exploited for travelling-wave
FIG. S5. Measurement and simulations illustrating the non-linear behavior of the first device (with two parallel microstrips) in the interference measurement presented in Fig. 1(b) in the main text. Signals are sent down both traces 1 and 3, with constant phase and variable power in trace 1, while in trace 3 the power is kept constant and the phase is varied. (a) Selected measurement curves showing the power output at trace 4 (opposite of trace 3) for different values of the power in trace 1. Non-linear effects manifest as a shift of the phase dependence and jumps that signal multi-stable states. (b) The simulation captures the shift of the phase dependence, from sinusoidal at low power $P_1$, to non-sinusoidal at intermediate $P_1$, to a shifted sinusoidal at large $P_1$. (c) Simulation of a device without non-linearity presented for contrast. In the linear device the phase dependence remains identical at all powers.

parametric amplifiers). Here, we will not consider those effects, but solve the nonlinear partial differential equation within a single-frequency ansatz (namely with the frequency of the CW-input). Thereby, it reduces to (coupled) ordinary differential equation (ODE) for $V(x)$ and $I(x)$ for each segment of our device.

In Sec. C we explained, how for the linear problem the Kirchhoff equations (cf. also Sec. B) reduce to a matrix equation Eq. (S24) for the amplitudes $A_q^j$ and $B_q^j$ of plane waves outgoing and incoming at each node $j$, which encode voltage and current in the linear case, cf. Eq. (S21). In the nonlinear case, the amplitudes $A_q^j$ and $B_q^j$ can still be used in similar fashion at the nodes (i.e. at the end points of each segment). However, the propagation along the segment and the relation between amplitudes at start and end is no longer trivially given by the phase factor of a propagating wave, $A_q^j = B_q^j e^{ik_j \delta^j}$, as in Eq. (S22), but rather has to be found by solving the corresponding ODE for each segment. This means that if nonlinear effects are included for a single segment $j$ between nodes $q_1$ and $q_2$, the two lines in the matrix equation Eq. (S24) corresponding to Eq. (S22) (and the corresponding equation
FIG. S6. Simulations of power distribution in the 7PMT, when introducing signal at 8.5GHz in the central trace at (a) −40dBm and (b) −90dBm. Colorbars include direction (positive is defined downwards and rightwards). Left(right) colorbar relates to couplers(traces) in both subfigures. Both figures are normalized according to the input power (i.e. leftmost cell in the central trace equals unity).

linking $B_{q1}^J$ to $A_{q2}^J$ are replaced by a nonlinear relation between the four amplitudes, which is implicitly defined by solving the corresponding ODE. The matrix equation Eq. (S24) thus becomes a nonlinear implicit equation.

To model the experimental results of Fig. 1(b), we consider nonlinear effects only for the couplers, where they are more pronounced. The nonlinear problem is solved in Matlab using a Broyden method, within which a standard od45-solver is used to find the amplitude relations along each segment.

F. Power propagation in the 7PMT

In the main letter’s Fig. 2(f) we presented the simulated propagation of power throughout the network, resembling observations from optical setup. In Fig. S6 we expand the simulation to show the propagation, also in the narrow couplers, too numerous to be shown in the main letter.

In particular, Fig. S6(a) displays the delay of transmission from the central trace, where the power is injected, to its neighbors. This is due to the high nonlinearity experienced by
most of the couplers linking this trace to the rest. In S6(b), where the introduced power is 5 orders of magnitude lower, fewer couplers are affected and the power transmits to adjacent traces earlier.

G. Simulation of the energy diffusion

Our simulations elaborate on future experiments possible with a lattice of coupled microwave resonators as the one we produced, though not experimentally possible with the given instantaneous bandwidth of the IQ mixers in our lab. By choosing the 15 highest peaks in the second energy band shown in the main text’s Fig. 3b (between 4.8 and 8 GHz) and their corresponding wave functions $\psi_m$ (presumed to be eigenmodes of the system), we simulate the evolution of

$$\rho_1 = \sum_m \alpha_m \psi_m$$  \hspace{1cm} (S26)

where $\rho_1$ denotes the state, where only one of the corner-resonators in the lattice is excited. Ideally, if $\psi_m$ was a complete set of orthonormal eigenmodes, we would expect $\psi_n \cdot \psi_n^\ast = \delta_{n,m}$. This would imply that

$$\alpha_m = \psi_m^\ast \cdot \rho_1$$  \hspace{1cm} (S27)

In reality, the main text’s Fig. 3b shows only modes with considerable energy in the two resonators used for input and output respectively, and as we described in Sec. C this is true for Fig. 3c too. Thus $\psi_m$ does not obey Eq. (S27), but approximates it as the unnormalized wavefunctions holds $|\psi_n|^2 > |\psi_n \cdot \psi_m |^2$ for $m \neq n$. The limitation of this approximation is visible in the main text’s Fig. 3e, where our attempt to excite only the first resonator also leads to weak excitations in other resonators. The evolution of the states over time and the propagation of the energy throughout the lattice is given by $\rho(t) = \sum_m \alpha_m \psi_m e^{-2\pi f_m t}$ and is depicted in the main text’s Fig. 3f-h. A video of the evolution is available online.

H. Simulation of a non-linear resonance in the 2D square lattice

The resonance studied in Figs. 4d,e is modeled as a resonance of a toy-model Fabry-Perot cavity with Duffing non-linearity. The relevant properties of the two scatterers (mirrors) defining the Fabry-Perot cavity are transmission amplitudes $t_1$ and $t_2$ and reflection amplitudes of waves inside the cavity, $r'_1$ and $r_2$. The amplitude of the input $a_{in}$ at one of the
cavity mirrors (port 1) is transmitted through the cavity and is read out as the output \( a_{\text{out}} \), such that \( a_{\text{out}} = S_{21} a_{\text{in}} \). The amplitude \( S_{21} \) models transmission through the much more complex resonant structure realized in the experiment. In our toy model, the transmission is given by
\[
S_{21} = \frac{|t_1||t_2|\, e^{i\phi}}{1 - |r_1'||r_2|e^{2iK_{\text{eff}}L}}.
\] (S28)
We have assumed the cavity is symmetric, \( |t_1| = |t_2| = t \) and \( |r_1'| = |r_2| = \sqrt{1-t^2} \), as asymmetry only impacts the absolute scale of measured powers.

Important to the model are the phases \( \phi \) and \( K_{\text{eff}}L \). The first models the phase accumulated when passing through the mirrors and the second, the phase accumulated crossing the cavity. Both phases are assumed linear in the input frequency \( \omega \) in the linear regime and account for a Duffing-type non-linearity,
\[
\phi = \frac{(\omega - \omega_{\text{res}})}{\alpha \gamma} \left( 1 - \beta \frac{\gamma}{\omega_{\text{res}}} \frac{|a_{\text{out}}|^2}{P_c} \right),
\] (S29)
\[
K_{\text{eff}}L = 2\pi \frac{\omega}{\omega_{\text{res}}} \left( 1 + \frac{\gamma}{\omega_{\text{res}}} \frac{|a_{\text{out}}|^2}{P_c} \right).
\] (S30)
Here we have introduced parameters that characterize the resonance: frequency \( \omega_{\text{res}} \), linewidth \( \gamma = t^2 \omega_{\text{res}} \), and critical output power \( P_c \) above which the Duffing curve becomes multiple valued. These can be directly extracted from the measurement. The two numerical parameters \( \alpha \) and \( \beta \) are the only fitting parameters, that are found to be of order unity. \((\alpha = 2 \text{ and } \beta = 1.6)\)

The simulated phase space plot (inset of Fig. 4d) is obtained as a parametric plot of the imaginary part of \( S_{21} \) versus its real part, while the simulated resonance curves (inset of Fig. 4e) are obtained by plotting \(|S_{21}|^2 = P_{\text{out}}/P_{\text{in}} \) versus frequency \( \omega \).

